



PATENT  
29936/37830

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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9/10/02  
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Applicants:

Park et al.

Serial No.: 10/036,156

For: Method of Forming a Metal  
Gate in a Semiconductor Device

Filed: December 26, 2001

Group Art Unit: 2813

Examiner: Chen

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August 29, 2002

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**AMENDMENT AND  
RESPONSE TO THE OFFICE ACTION DATED AUGUST 2, 2002**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office action dated August 2, 2002, please add new claims 13 and 14, and consider the following remarks in traversal of the election of species requirement.

In the Claims:

Please add new claims 13 and 14 as follows:

13. (New) The method of claim 1, wherein the metal film is deposited by an atomic layer deposition (ALD) process.

14. (New) The method of claim 13, wherein said barrier metal film is selected from the group consisting of TiN, TiAlN, TaN, MoN and WN.

**REMARKS**

The Office action dated March 21, 2002 has been carefully considered.

In view of the following remarks, all pending claims are in condition for